

DPSS84 P-Channel MOSFET

General description

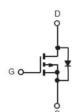
P-Channel Enhancement Mode Field Effect Transistor

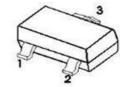
Features:

- V_{DS}: -50V
- I_D: -0.13A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <8 ohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) < 10 ohm
- Trench Power LV MOSFET technology
- Low RDS(ON)
- Low Gate Charge

Applications:

- Video monitor
- Power managemen





- 1. Gate
- 2. Source
- 3. Drain

Package: SOT-23

Device Type	Device Marking		
DPSS84	B84		

Absolute Maximum Ratings (TA=25°Cunless otherwise noted)

Parameter	Symbol	Maximum	Unit	
Drain-source Voltage	$V_{ extsf{DS}}$	-50	V	
Gate-source Voltage	V_{GS}	±20	V	
Drain Current	I _D	-0.13	А	
Pulsed Drain Current ^A	Ірм	-0.68	А	
Total Power Dissipation @ T _A =25℃	P_{D}	225	mW	
Thermal Resistance Junction-to-Ambient ^B	R_{θ} JA	556	°C/W	
Junction and Storage Temperature Range	TJ ,Tstg	-55∼+150	°C	

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DPSS84



Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units			
Static Parameter									
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-50			V			
Zero Gate Voltage Drain Current	Ioss	V _{DS} =-50V,V _{GS} =0V,T _C =25°C			-1	μA			
Gate-Body Leakage Current	lgss	V_{GS} = ± 20 V, V_{DS} =0V			±100	nA			
Gate Threshold Voltage	V _{GS(th)}	V_{DS} = V_{GS} , I_D =-250 μ A	-0.9	-1.4	-2.0	٧			
Static Drain-Source On-Resistance	2	V _{GS} = -10V, I _D =-0.13A		4.0	8	- Ω			
	RDS(ON)	V _{GS} = -4.5V, I _D =-0.1A		4.2	10				
Diode Forward Voltage	V _{SD}	I _S =-0.13A,V _{GS} =0V			-1.2	٧			
Maximum Body-Diode Continuous Current	Is				-0.17	Α			
Dynamic Parameters									
Input Capacitance	C _{iss}	V_{DS} =-30V, V_{GS} =0V,f=1MHZ		30		pF			
Output Capacitance	C _{oss}			10					
Reverse Transfer Capacitance	C _{rss}			5					
Switching Parameters									
Turn-on Delay Time	t _{D(on)}	V_{GS} =-4.5V, V_{DD} =-30V, I_{D} =-0.15A, R_{GEN} =2.5 Ω		2.5		ns ns			
Turn-on Rise Time	t _r			1					
Turn-off Delay Time	t _{D(off)}			16					
Turn-off Fall Time	t _f			8					

Note

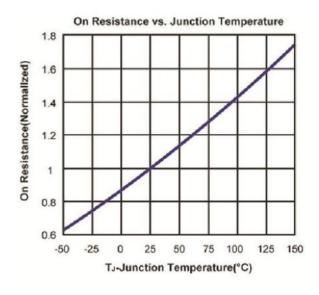
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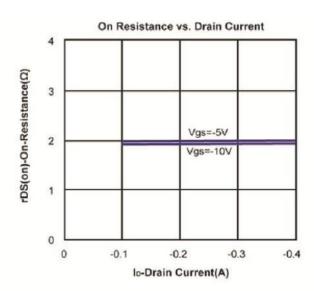
A. Pulse Test: Pulse Width \leq 300us, Duty cycle \leq 2%.

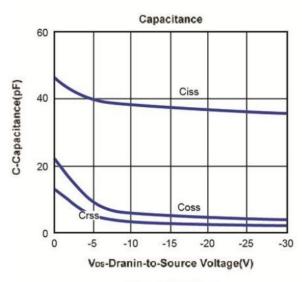
B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

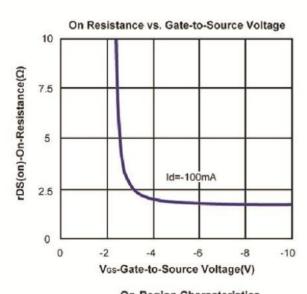


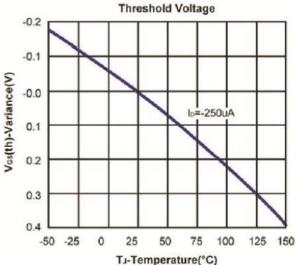
Typical Performance Characteristics

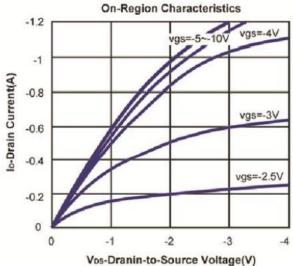






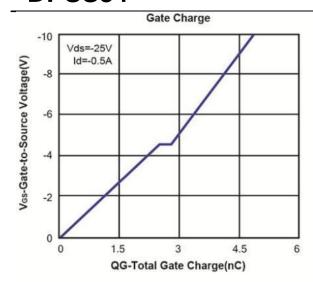


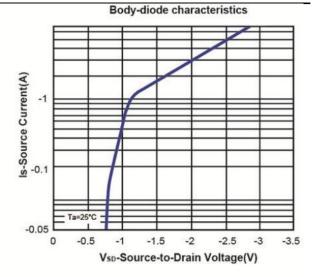


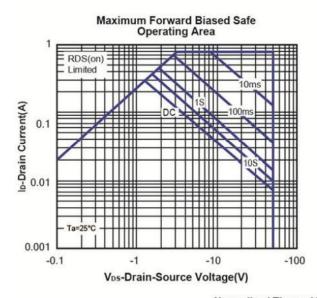


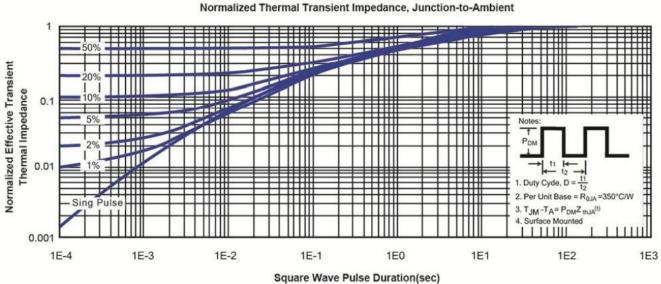
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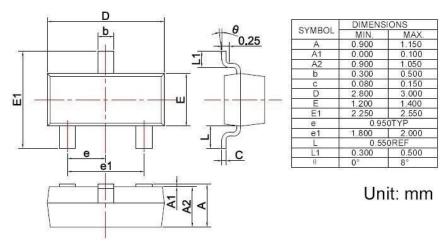




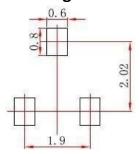
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SOT-23 Package Outline Dimensions



Precautions: PCB Design



Note:

- 1.Controlling dimension: in millimeters.
 2.General tolerance: ± 0.05mm.
- 3. The pad layout is for reference purposes only.

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